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Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-4CSH01-M3/86A</u>

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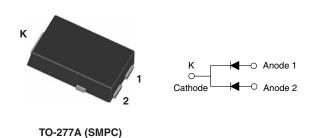




VS-4CSH01-M3

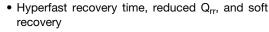
Vishay Semiconductors

Hyperfast Rectifier, 2 x 2 A FRED Pt®



PRODUCT SUMMARY				
Package	TO-277A (SMPC)			
I _{F(AV)}	2 x 2 A			
V _R	100 V			
V _F at I _F	0.75 V			
t _{rr (typ.)}	24 ns			
T _J max.	175 °C			
Diode variation	Dual die			

FEATURES





• 175 °C maximum operating junction temperature

Specified for output and snubber operation

ROHS COMPLIANT

FREE

Low forward voltage drop

· Low leakage current

 Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

• Meets JESD 201 class 2 whisker test

 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, as high frequency rectifiers and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage		V_{RRM}		100	V	
Average rectified forward current	per device	I _{F(AV)}	T _{Sp} = 165 °C	4	A	
	per diode			2		
Nia a manaditi a manada ma	per device	- I _{FSM}	T _J = 25 °C	90	A	
Non-repetitive peak surge current	per diode			50		
Operating junction and storage temperatures		T_J , T_{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	100	-	-	
Forward voltage, per diode V _F	M	I _F = 2 A	-	0.88	0.95	V
	VF	I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current, per diode	I _R	V _R = V _R rated	-	-	2	
		T _J = 125 °C, V _R = V _R rated	-	0.5	8	μΑ
Junction capacitance	C _T	V _R = 100 V	-	8	-	pF

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Datasheet of VS-4CSH01-M3/86A - DIODE HFAST REC 100V 2A TO277A

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
			$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		24	-	
Reverse recovery time t_{rr}		$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	24	
	ι _{rr}	T _J = 25 °C	I _F = 2 A dI _F /dt = 200 A/μs V _R = 160 V	-	16	-	ns
		T _J = 125 °C		-	22	-	
Peak recovery current I _{RRM}	I _{RRM}	T _J = 25 °C		-	2	-	^
		T _J = 125 °C		-	3	-	A
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	16	-	nC
	T _J = 125 °C		-	30	-	nC nC	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J , T_{Stg}		-65	-	175	°C
Thermal resistance, junction to solder pad, per diode	R _{thJ-Sp}		-	4.5	5.5	°C/W
Approximate weight				0.1		g
Approximate weight				0.0035		OZ.
Marking device		Case style TO-277A (SMPC)		JC	H1	

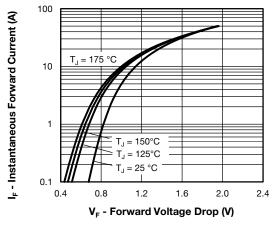


Fig. 1 - Typical Forward Voltage Drop Characteristics

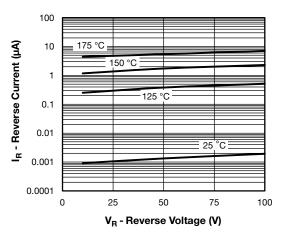


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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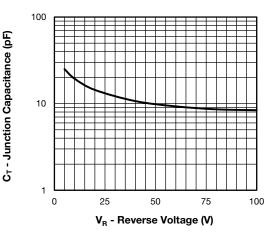


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

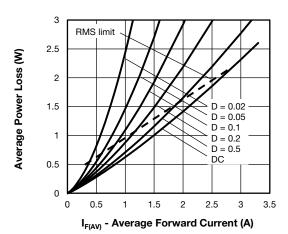


Fig. 5 - Forward Power Loss Characteristics

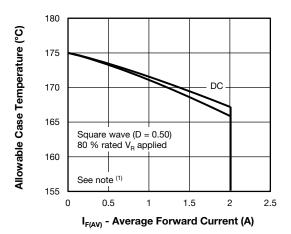


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

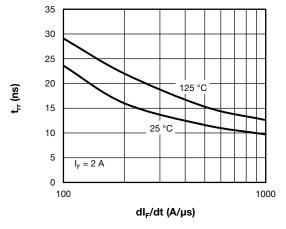


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

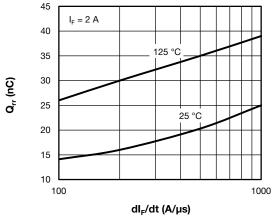


Fig. 7 - Typical Stored Charge vs. dl_E/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 5); $Pd_{REV} = Inverse power loss = V_{R1} \times I_{R}$ (1 - D); I_R at $V_{R1} = rated V_{R1}$

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Datasheet of VS-4CSH01-M3/86A - DIODE HFAST REC 100V 2A TO277A

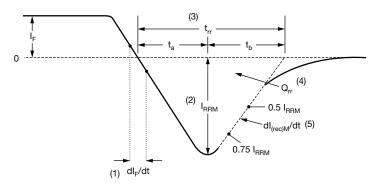
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- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

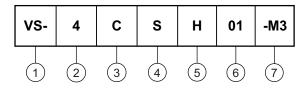
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- Current rating (4 = 4 A)
- Circuit configuration:
 - C = common cathode
- S = SMPC package
- Process type,
 - H = hyperfast recovery
- 6 Voltage code (01 = 100 V)
- 7 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-4CSH01-M3/86A	1500	1500	7" diameter plastic tape and reel			
VS-4CSH01-M3/87A	6500	6500	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95570			
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			

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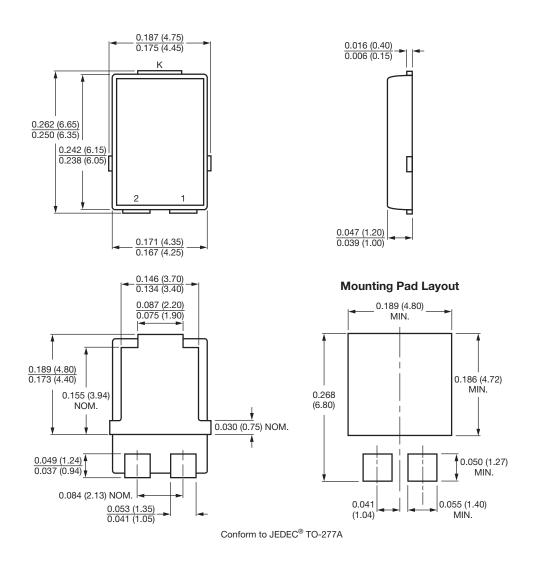


Outline Dimensions

Vishay Semiconductors

TO-277A (SMPC)

DIMENSIONS in inches (millimeters)





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